AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions, and listings, of claims in the application.

Claims 1-6 (Cancelled).

7. (Currently Amended) A semiconductor laser device fabricating method including:

forming a first cladding layer of a first conductivity type, an active layer having a quantum well structure, and a first second cladding layer of a second conductivity type successively on a semiconductor substrate of the first conductivity type;

forming on the first second cladding layer a mask pattern for impurity implantation, having an opening in a region where a resonator facet of a semiconductor laser device is to be formed;

disordering a region of the active layer near the resonator facet by introducing impurities using the mask pattern as a mask;

applying pump light to the disordered region and to a non-disordered region of the active layer to generate photoluminescence therefrom, ~~and~~ measuring ~~wavelength~~ wavelengths of the photoluminescence ~~for~~ from the disordered region and from the non-disordered region, and predicting a catastrophic optical damage (COD) ~~degradation~~ power level that the laser device, when completed, can withstand based on a blue shift between the wavelengths of the photoluminescence from the disordered region and the non-disordered region;

forming a second second cladding layer of the second conductivity type on said first second cladding layer, after removing the mask pattern;

forming on said second second cladding layer a stripe-shaped mask pattern, opposed to the disordered region of the active layer, and extending across the first and second second cladding layers, the stripe-shaped mask pattern extending in a resonator lengthwise direction; and

forming an optical waveguide including the second second cladding layer with the stripe-shaped mask pattern used as a mask.

8. (Currently Amended) The semiconductor laser device fabricating method according to claim 7, wherein~~, if~~ the semiconductor laser device produces light having a wavelength in the range of 770 to 810 nm,~~if~~ λ dpl denotes, in nm, the wavelength of photoluminescence generated by application of pump light to the disordered region of the active layer,~~if~~ λ apl represents, in nm, the wavelength of photoluminescence generated by application of pump light to the non-disordered region of the active layer, and~~if a blue shift amount~~ λ bl, in nm, is equal to λ apl - λ dpl, ~~then~~ including determining that the COD power level that the laser device, when completed, can withstand has been increased when λ bl~~,~~ ≥ 20~~when the pump light is applied to the disordered region~~.

9. (Currently Amended) The semiconductor laser device fabricating method according to claim 8, wherein,~~if~~ when Pcod denotes, in mW, the COD power level~~of~~ that the laser device can withstand,

$$(Pcod - 85)/5.6 \leqq \lambda bl \leqq (Pcod - 135.0)/1.3.$$